# ne<mark>x</mark>peria

#### Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of <u>http://www.nxp.com</u>, <u>http://www.philips.com/</u> or <u>http://www.semiconductors.philips.com/</u>, use <u>http://www.nexperia.com</u>

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use **salesaddresses@nexperia.com** (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

Should be replaced with:

- © Nexperia B.V. (year). All rights reserved.

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

NPN/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

Rev. 01 — 17 February 2005

Product data sheet

### 1. Product profile

#### **1.1 General description**

NPN/PNP resistor-equipped transistors.

Table I. FIGUULLOVELVIEW	Table	1:	Product	overview
--------------------------	-------	----	---------	----------

Type number	Package	Package F		NPN/NPN	
	Philips	JEITA	complement	complement	
PEMD19	SOT666	-	PEMB19	PEMH19	
PUMD19	SOT363	SC-88	PUMB19	PUMH19	

#### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place cost

#### **1.3 Applications**

- Low current peripheral driver
- Control of IC inputs
- Replacement of general-purpose transistors in digital applications

#### 1.4 Quick reference data

#### Table 2: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	50	V
lo	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ



*006aaa269* 

NPN/PNP resistor-equipped transistors; R1 = 22 kΩ, R2 = open

# 2. Pinning information

Table 3:	Pinning				
Pin	Description	Simplified outline	Symbol		
1	GND (emitter) TR1				
2	input (base) TR1	6 5 4	6 5 4		
3	output (collector) TR2				
4	GND (emitter) TR2				
5	input (base) TR2				
6	output (collector) TR1	001aab555			
			1 2 3		

### 3. Ordering information

Table 4: Ordering information					
Type number Package					
	Name	Description	Version		
PEMD19	-	plastic surface mounted package; 6 leads	SOT666		
PUMD19	SC-88	plastic surface mounted package; 6 leads	SOT363		

### 4. Marking

Table 5: Marking codes		
Type number	Marking code [1]	
PEMD19	6E	
PUMD19	T4*	

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

#### NPN/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

# 5. Limiting values

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor v	with negative polar	ity		
V <sub>CBO</sub>	collector-base voltage	open emitter	-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V
lo	output current (DC)		-	100	mA
I <sub>CM</sub>	peak collector current		-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		[1] [2] _	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
Per device	)				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1] [2] _	300	mW

[1] Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

### 6. Thermal characteristics

Table 7:	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		<u>[1]</u> <u>-</u>	-	625	K/W
Per device	e					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	$T_{amb} \le 25 \ ^{\circ}C$				
	SOT363		<u>[1]</u> -	-	416	K/W
	SOT666		<u>[1]</u> <u>[2]</u> _	-	416	K/W

[1] Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

[2] Reflow soldering is the only recommended soldering method.

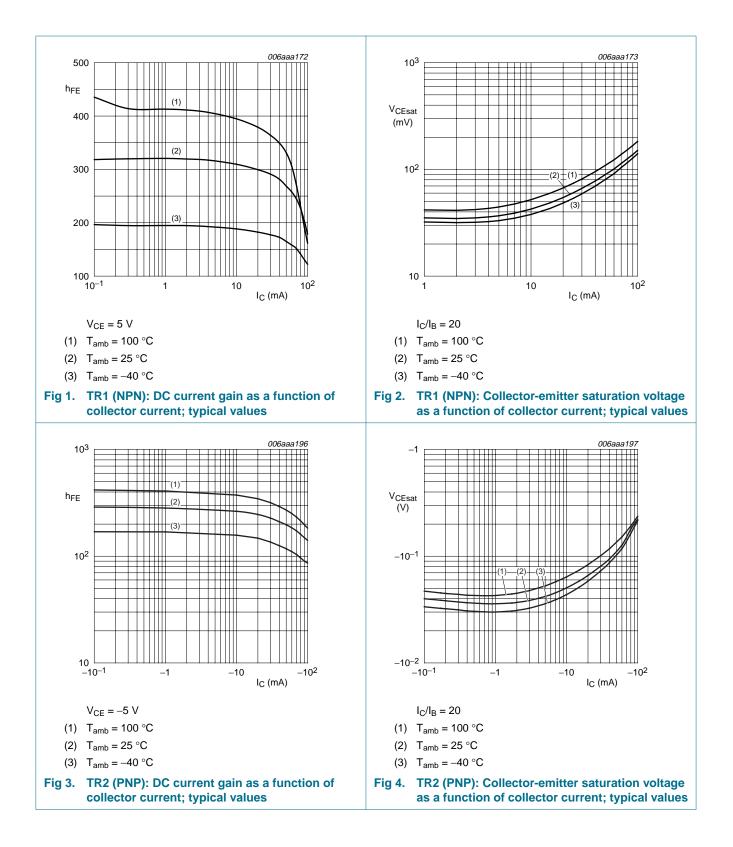
NPN/PNP resistor-equipped transistors; R1 = 22 kΩ, R2 = open

# 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor; for the PNP transis	tor with negative polarity				
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}$	-	-	1	μA
cut-off current		$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A};$ T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; \text{ I}_{C} = 1 \text{ mA}$	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = 10 mA; $I_{B}$ = 0.5 mA	-	-	150	mV
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; \text{ I}_{E} = \text{i}_{e} = 0 \text{ A};$ f = 1 MHz				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	pF

# PEMD19; PUMD19

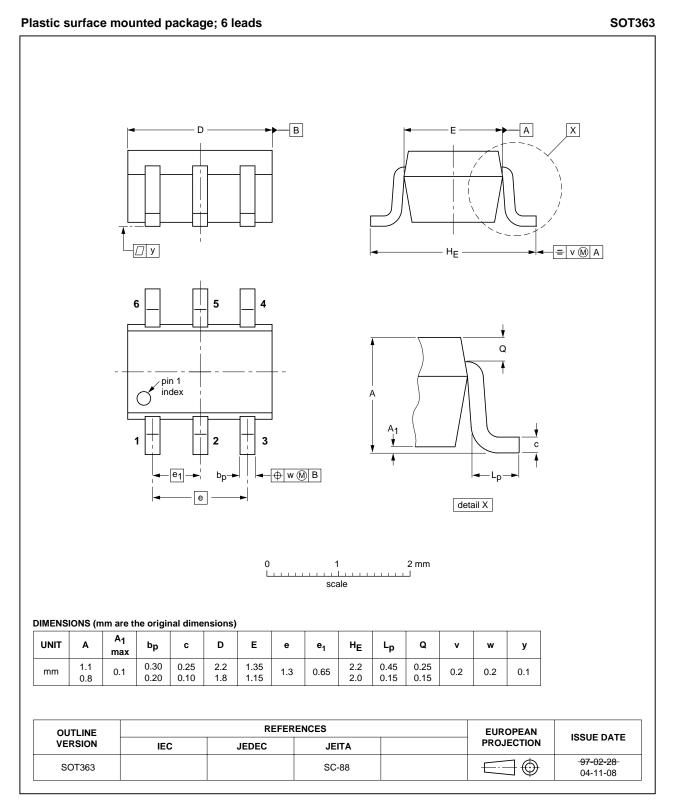
#### NPN/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open



PEMD19; PUMD19

NPN/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

### 8. Package outline



#### Fig 5. Package outline SOT363 (SC-88)

PEMD19; PUMD19

NPN/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

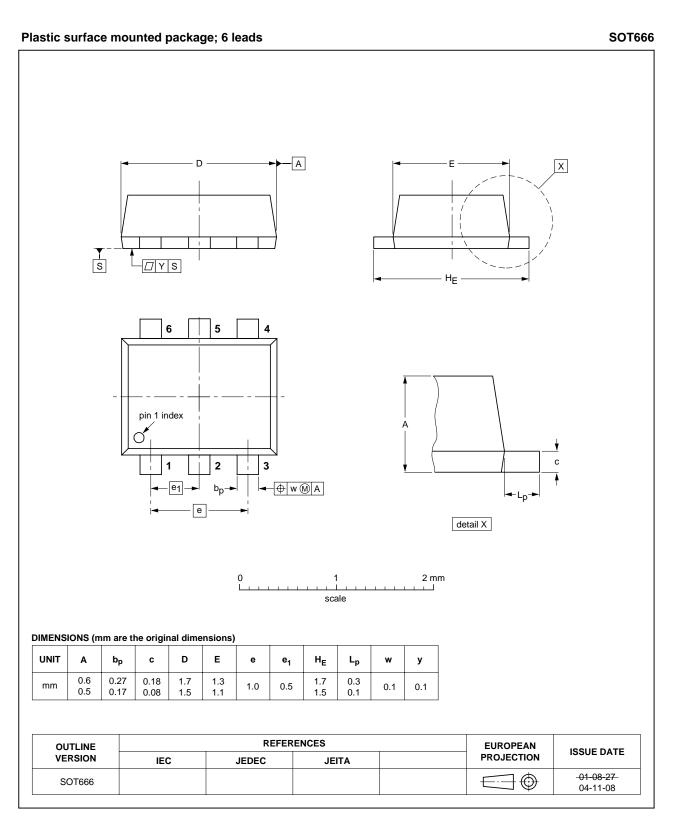


Fig 6. Package outline SOT666

9397 750 14408 Product data sheet NPN/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

# 9. Packing information

#### Table 9: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing of	quantity	
			3000	4000	10000
PEMD19	SOT666	4 mm pitch, 8 mm tape and reel	-	-115	-
PUMD19	SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-	-135
PUMD19	SOT363	4 mm pitch, 8 mm tape and reel; T2	-125	-	-165

[1] For further information and the availability of packing methods, see Section 14.

[2] T1: normal taping

[3] T2: reverse taping

NPN/PNP resistor-equipped transistors; R1 = 22 kΩ, R2 = open

# **10. Revision history**

Table 10: Revision history					
Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PEMD19_PUMD19_1	20050217	Product data sheet	-	9397 750 14408	-

NPN/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

### 11. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

# **12. Definitions**

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

**Application information** — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

### **13. Disclaimers**

Life support — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

**Right to make changes** — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

# **14. Contact information**

For additional information, please visit: http://www.semiconductors.philips.com For sales office addresses, send an email to: sales.addresses@www.semiconductors.philips.com

# PEMD19; PUMD19

NPN/PNP resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = open

### **15. Contents**

1	Product profile 1
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 3
7	Characteristics 4
8	Package outline 6
9	Packing information 8
10	Revision history9
11	Data sheet status 10
12	Definitions 10
13	Disclaimers 10
14	Contact information 10



#### © Koninklijke Philips Electronics N.V. 2005

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Date of release: 17 February 2005 Document number: 9397 750 14408

**Published in The Netherlands** 

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - Pre-Biased category:

Click to view products by Nexperia manufacturer:

Other Similar products are found below :

RN1607(TE85L,F) DTA124GKAT146 DTA144WETL DTA144WKAT146 DTC113EET1G DTC115TETL DTC115TKAT146 DTC124TETL DTC144ECA-TP DTC144VUAT106 MUN5241T1G BCR158WH6327XTSA1 NSBA114TDP6T5G NSBA143ZF3T5G NSBC114YF3T5G NSBC123TF3T5G SMUN5235T1G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F) RN4605(TE85L,F) TTEPROTOTYPE79 DDTC114EUAQ-7-F EMH15T2R SMUN2214T3G SMUN5335DW1T1G NSBC114TF3T5G NSBC143ZPDP6T5G NSVMUN5113DW1T3G SMUN5230DW1T1G SMUN5133T1G SMUN2214T1G DTC114EUA-TP NSBA144EF3T5G NSVDTA114EET1G 2SC2223-T1B-A 2SC3912-TB-E SMUN5237DW1T1G SMUN5213DW1T1G SMUN5114DW1T1G SMUN2111T1G NSVDTC144EM3T5G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G